

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Previously Presented) A method for removing a resist pattern, comprising:  
forming a metal film over a substrate;  
forming a resist pattern of a positive resist composition containing a photosensitizer over the metal film;  
etching the metal film by using the resist pattern;  
irradiating the resist pattern with a light having a photosensitive wavelength region of the photosensitizer to react the photosensitizer in the resist pattern to the light after etching the metal film; and  
after irradiating the resist pattern, removing the resist pattern by using a resist stripper which dissolves and removes the resist pattern.

2. (Currently Amended) A method for removing a resist pattern, comprising:  
forming a metal film over a substrate;  
forming a resist film of a positive resist composition containing a photosensitizer;  
exposing the resist film;  
developing the resist film to form forming a resist pattern of a positive resist composition containing a photosensitizer over the metal film by using a developer;  
etching the metal film by using the resist pattern;  
removing the resist pattern by using a resist stripper which dissolves and removes the resist pattern after etching the metal film;  
irradiating a residue of the resist pattern with a light having a photosensitive wavelength region of the photosensitizer to react the photosensitizer in the residue of the resist pattern to the light after removing the resist pattern; and

after the irradiating the residue of the resist pattern, removing the residue of the resist pattern by using [[a]] the developer which dissolves and removes the residue of the resist pattern.

3-4. (Canceled)

5. (Previously Presented) A method for removing a resist pattern according to claim 1, wherein the positive resist composition containing the photosensitizer is a diazonaphthoquinone (DNQ)-novolac resin type, and wherein the photosensitizer is diazonaphthoquinone (DNQ).

6. (Previously Presented) A method for removing a resist pattern according to claim 2, wherein the positive resist composition containing the photosensitizer is a diazonaphthoquinone (DNQ)-novolac resin type, and wherein the photosensitizer is diazonaphthoquinone (DNQ).

7-8. (Canceled)

9. (Currently Amended) A method for removing a resist pattern according to claim [[2]] 1, wherein the metal film forms an electrode of a thin film transistor.

10. (Currently Amended) A method for manufacturing a semiconductor device according to claim [[3]] 2, wherein the metal film forms an electrode of a thin film transistor.

11-19. (Canceled)

20. (Previously Presented) A method for removing a resist pattern according to claim 1, wherein the substrate is selected from the group consisting of a glass, a quartz, a semiconductor, a plastic, a plastic film, a metal, a glass-epoxy resin, and a ceramic.

21. (Previously Presented) A method for removing a resist pattern according to claim 2, wherein the substrate is selected from the group consisting of a glass, a quartz, a semiconductor, a plastic, a plastic film, a metal, a glass-epoxy resin, and a ceramic.

22-23. (Canceled)

24. (Previously Presented) A method for removing a resist pattern according to claim 1, wherein the metal film comprises a material selected from the group consisting of aluminum, titanium, molybdenum, tantalum, and tungsten.

25. (Previously Presented) A method for removing a resist pattern according to claim 2, wherein the metal film comprises a material selected from the group consisting of aluminum, titanium, molybdenum, tantalum, and tungsten.

26-27. (Canceled)

28. (Previously Presented) A method for removing a resist pattern according to claim 1, wherein the resist stripper has a mixture of 2-aminoethanol and a glycol ether as a composition.

29. (Previously Presented) A method for removing a resist pattern according to claim 2, wherein the resist stripper has a mixture of 2-aminoethanol and a glycol ether as a composition.

30-31. (Canceled)

32. (Previously Presented) A method for removing a resist pattern according to claim 1, wherein the light has a multiple wavelengths within the range of photosensitive wavelength region of the photosensitizer.

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33. (Previously Presented) A method for removing a resist pattern according to claim 2, wherein the light has a multiple wavelengths within the range of photosensitive wavelength region of the photosensitizer.

34-35. (Canceled)